

Amendments to the Claims

1. (*Currently Amended*) A method for fabrication of in-laid metal structures, comprising the steps of :

- [[[-]]] providing a substrate with a dielectric material on top thereof,
- [[[-]]] depositing a protection layer on top of the dielectric material,
- [[[-]]] depositing a sacrificial layer on top of the protection layer, the sacrificial layer having a mechanical strength which is lower than the mechanical strength of the protection layer,
- [[[-]]] making an opening through the sacrificial layer, through the protection layer and into the dielectric material,
- [[[-]]] depositing a barrier layer in the opening and on the sacrificial layer
- [[[-]]] depositing metal material on the barrier layer, the metal material filling the opening,
- [[[-]]] removing portions of the metal material existing beyond the opening by means of polishing, and
- [[[-]]] removing the barrier layer and the sacrificial layer in one polishing step.

2. (*Original*) A method according to claim 1, wherein the portions of the metal material existing beyond the opening, the barrier layer and the sacrificial layer are removed in one polishing step.

3. (*Original*) A method according to claim 1, wherein the one polishing step makes use of one consumable set.

4. (*Original*) A method according to claim 1, wherein the polishing step is a step of chemical mechanical polishing (CMP).

5. (*Original*) A method according to claim 1, wherein the adhesion between the sacrificial layer and the protection layer is weaker than the adhesion between the protection layer and the dielectric material.

6. *(Original)* A method according to claim 1, wherein the sacrificial layer is a low-k material.
7. *(Original)* A method according to claim 1, wherein the dielectric material comprises a low-k material.
8. *(Currently Amended)* A method according to claim 1, wherein the step of depositing metal material comprises depositing copper, ~~aluminum~~, aluminum, silver, gold, or tungsten.
9. *(Original)* A method according to claim 1, wherein the step of depositing metal material comprises depositing metal material by chemical vapor deposition.
10. *(Original)* A method for manufacturing a semiconductor device using a method for fabrication of in-laid metal structures according to claim 1.